

# 2SJ356C

R07DS1260EJ0300

Rev.3.00

Aug 17, 2015

## P-CHANNEL MOSFET FOR SWITCHING

### Description

The 2SJ356C, P-channel vertical type MOSFET designed for general-purpose switch, is a device which can be driven directly by a 4.0 V power source.

### Features

- Directly driven by a 4.0 V power source.
- Low on-state resistance  
 $R_{DS(on)1} = 388 \text{ m}\Omega \text{ MAX. (} V_{GS} = -10 \text{ V, } I_D = -1.0 \text{ A)}$   
 $R_{DS(on)2} = 514 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -1.0 \text{ A)}$   
 $R_{DS(on)3} = 556 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -1.0 \text{ A)}$

### Ordering Information

Part Number	Lead Plating	Packing	Package
2SJ356C-T1-AZ/AY	-AZ : Sn-Bi , -AY : Pure Sn	1000p/Reel	SC-62 (3p PoMM)

**Remark** "-AZ/AY" indicates Pb-free. This product does not contain Pb in external electrode and other parts.

### Marking XE

### Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ )

Drain to Source Voltage ( $V_{GS} = 0 \text{ V}$ )	$V_{DSS}$	-60	V
Gate to Source Voltage ( $V_{DS} = 0 \text{ V}$ )	$V_{GSS}$	$\pm 20$	V
Drain Current (DC)	$I_{D(DC)}$	$\pm 2.0$	A
Drain Current (pulse) <sup>Note1</sup>	$I_{D(pulse)}$	$\pm 6.0$	A
Total Power Dissipation <sup>Note2</sup>	$P_T$	2.0	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**Note1**  $PW \leq 10 \text{ ms}$ , Duty Cycle  $\leq 1\%$

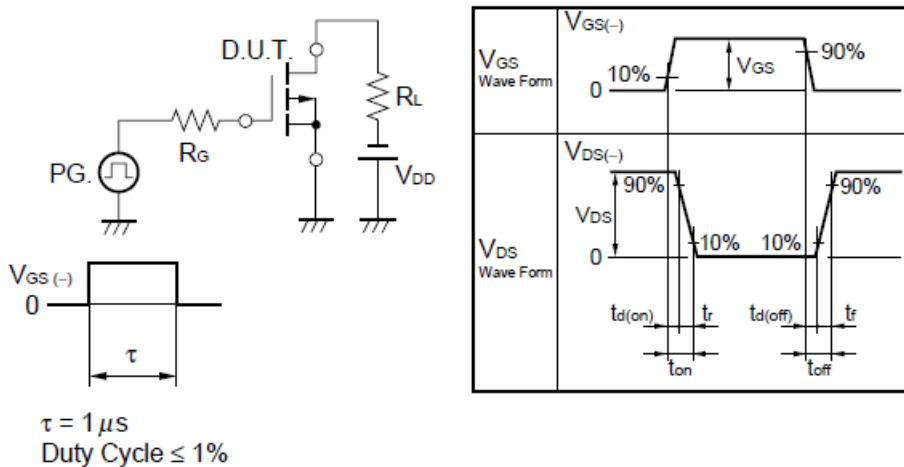
**Note2**  $16 \text{ cm}^2 \times 0.7\text{mm}$ , ceramic substrate used

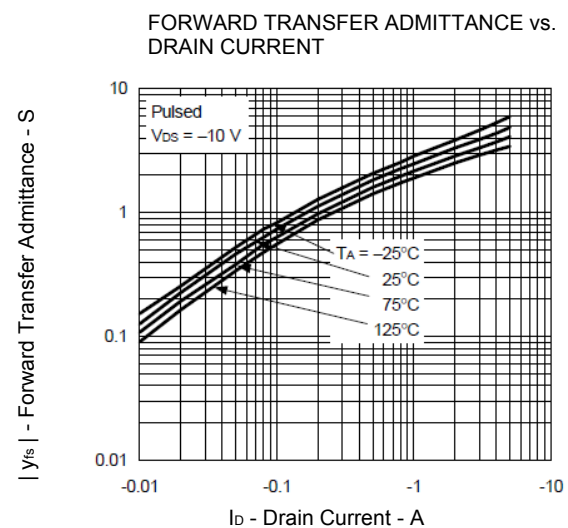
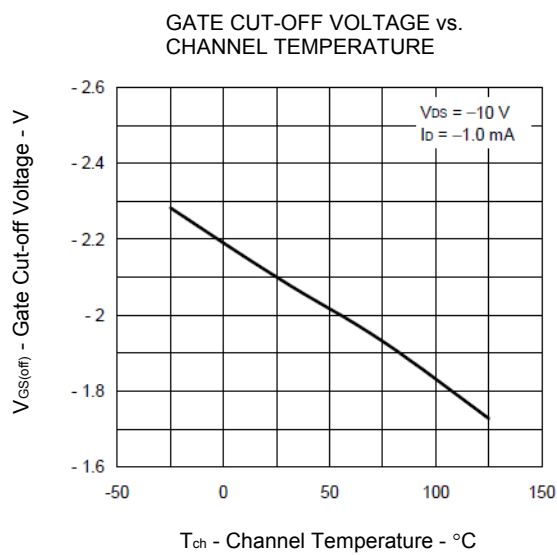
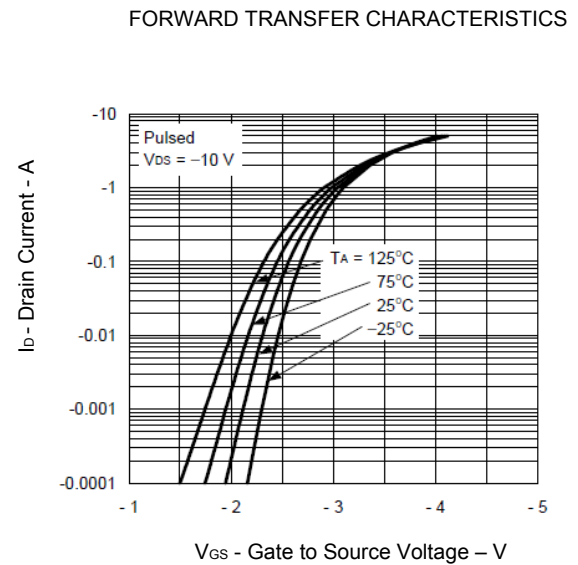
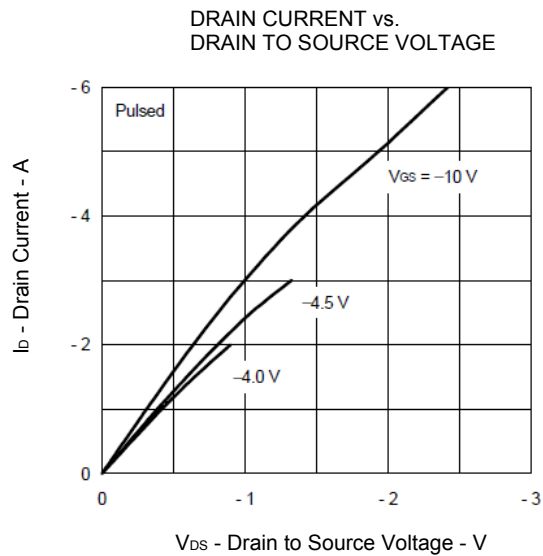
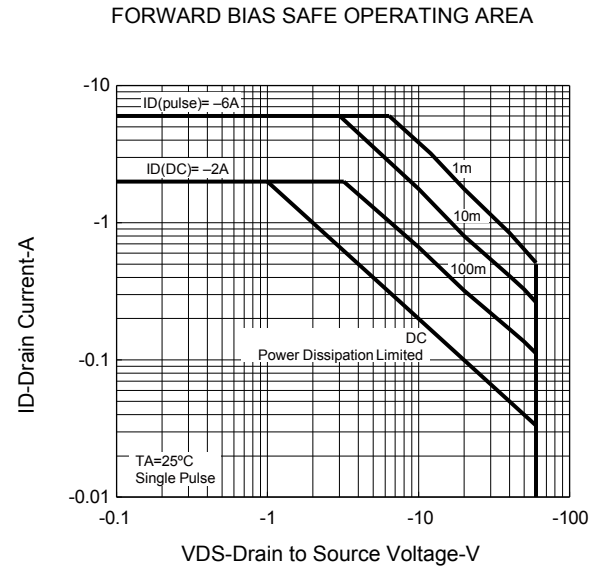
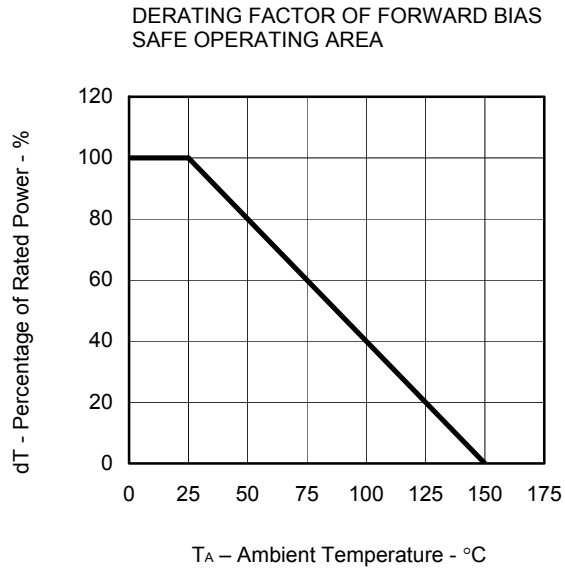
Electrical Characteristics (T<sub>A</sub> = 25°C)

Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V			-1	μA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μA
Gate to Source Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1 mA	-1.5	-2.1	-2.5	V
Forward Transfer Admittance <b>Note</b>	y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.0 A	1.0	2.5		S
Drain to Source On-state Resistance <b>Note</b>	R <sub>DS(on)1</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -1.0 A		310	388	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1.0 A		385	514	mΩ
	R <sub>DS(on)3</sub>	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -1.0 A		417	556	mΩ
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V,		255		pF
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V,		45		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1.0 MHz		17		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -30 V,		17		ns
Rise Time	t <sub>r</sub>	I <sub>D</sub> = -1 A,		9		ns
Turn-off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> = -10 V,		92		ns
Fall Time	t <sub>f</sub>	R <sub>G</sub> = 10 Ω		37		ns
Total Gate Charge	Q <sub>G</sub>	I <sub>D</sub> = -1.5 A, V <sub>DD</sub> = -48 V, V <sub>GS</sub> = -10 V		8.2		nC
Body Diode Forward Voltage <b>Note</b>	V <sub>F(S-D)</sub>	I <sub>F</sub> = 1.5 A, V <sub>GS</sub> = 0 V		0.86		V

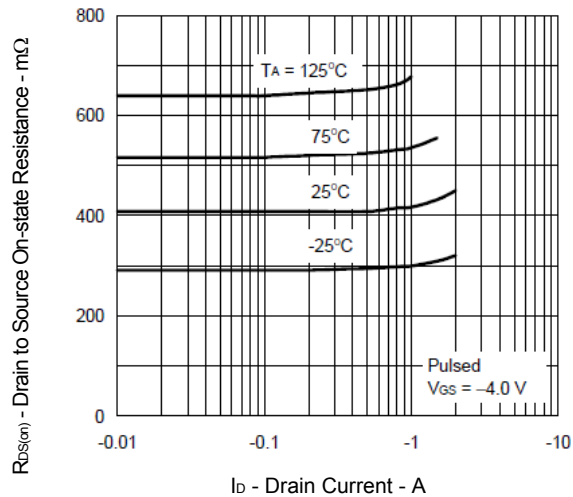
**Note** Pulsed

## Test Circuit Switching Time

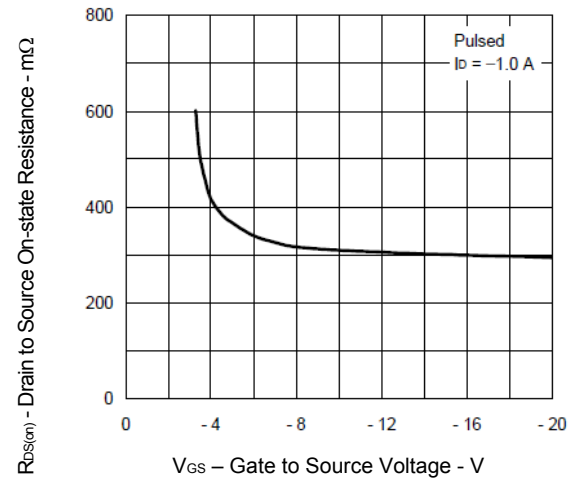


Typical Characteristics ( $T_A = 25^\circ\text{C}$ )

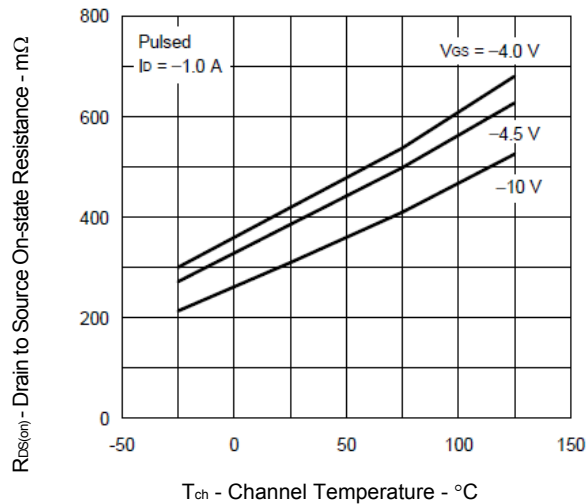
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



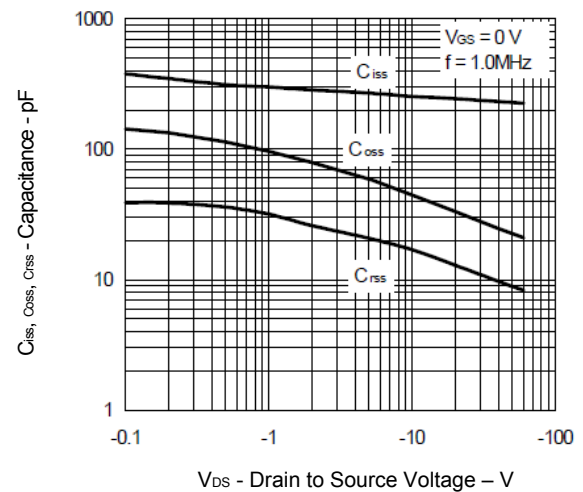
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



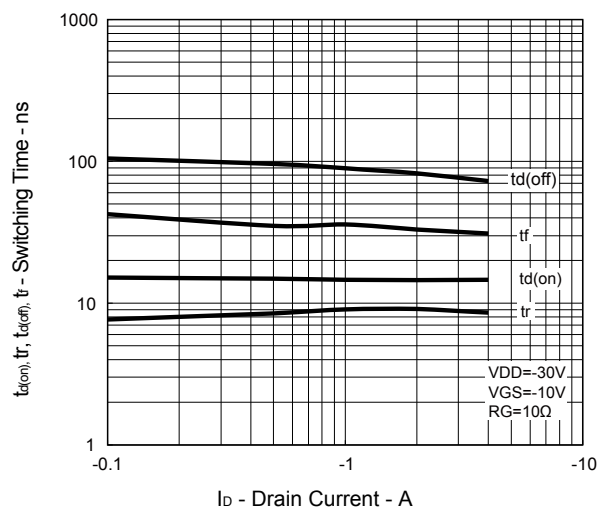
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



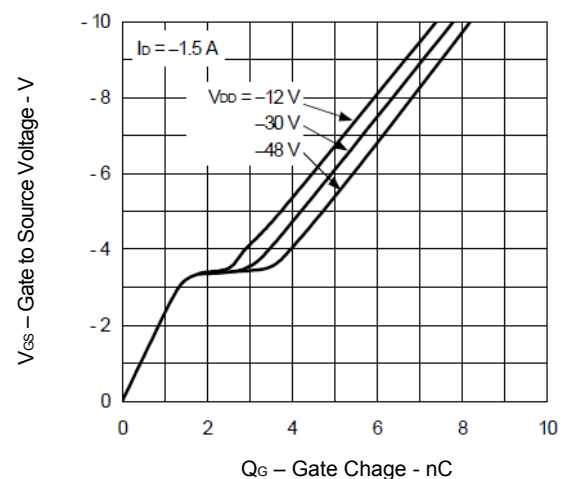
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

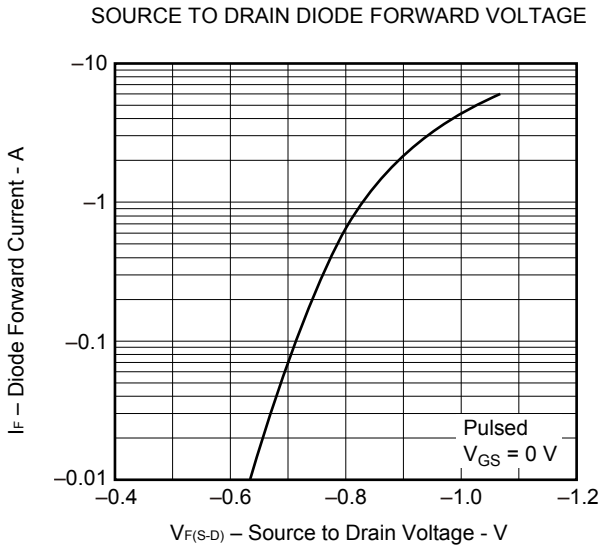


SWITCHING CHARACTERISTICS



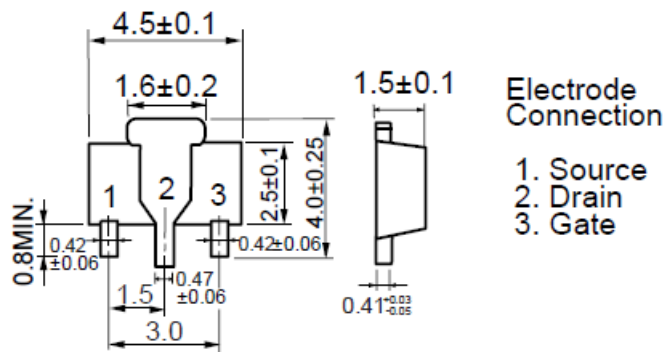
DYNAMIC INPUT CHARACTERISTICS



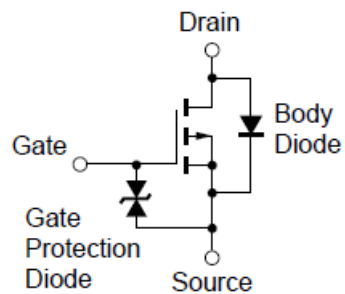


## Package Drawings (Unit: mm)

## SC-62 (3pPoMM)



## Equivalent Circuit



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

	<b>2SJ356C</b>
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Rev.	Date	Description	
		Page	Summary
1.00	Sep , 2013	–	First Edition Issued
1.10	Nov , 2013	2	Test Circuit
1.20	Mar , 2015	1 , 2	Add the Note2 , Change of tr and tf typical value
2.00	Jun , 2015	3	Added FORWARD BIAS SAFE OPERATING AREA
		4	Changed SWITCHING CHARACTERISTICS
3.00	Aug , 2015	3	Changed FORWARD BIAS SAFE OPERATING AREA
		4	Changed SWITCHING CHARACTERISTICS
		5	Changed SOURCE TO DRAIN DIODE FORWARD VOLTAGE

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